

# 17-21 GHz High Output TOI Packaged Amplifier

## TGA4530-SM

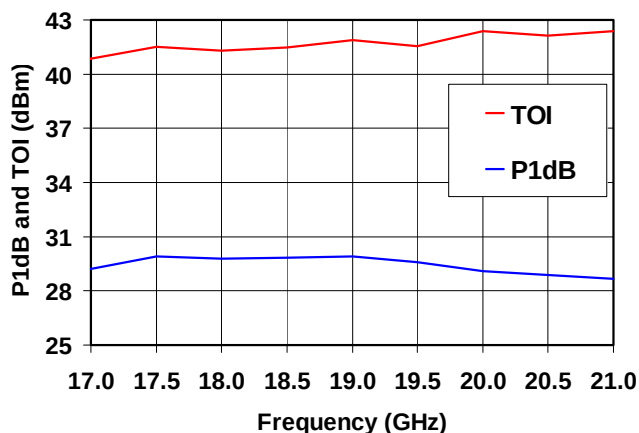
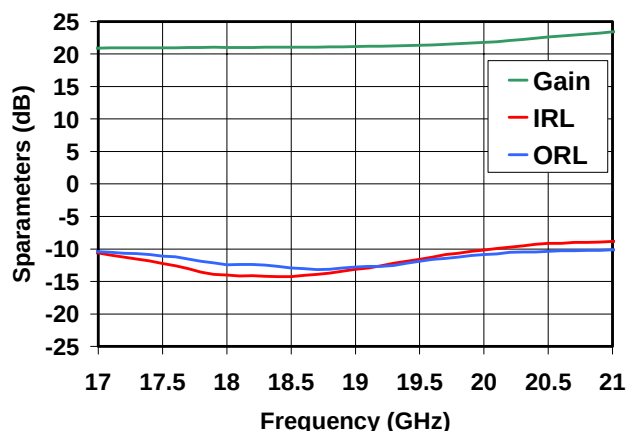


### Key Features

- Frequency Range: 17 - 21 GHz
- 41dBm Nominal Output TOI
- 21 dB Nominal Gain
- 29 dBm Nominal P1dB
- 12 dB Nominal Return Loss
- Bias 6 V @ 825 mA
- 4 x 4 QFN with 20 leads
- Package Dimensions 4.0 x 4.0 x 1.2 mm

### Measured Fixtured Data

Bias Conditions:  $V_d = 6V$ ,  $I_d = 825mA$



### Primary Applications

- Point-to-Point Radio
- Point-to-Multipoint Communications
- K Band Sat-Com

### Product Description

The TriQuint TGA4530 is a High Power Amplifier MMIC for 17 – 21GHz applications. The part is designed using TriQuint's proven standard 0.25 um power pHEMT production process

The TGA4530 nominally provides 29 dBm saturated output power at the 1 dB compression point and 41dBm OTOI for bias of 6V, 825mA. The typical gain is 22dB.

The part is ideally suited for low cost emerging markets such as Point-to-Point Radio, Point-to-Multi Point Communications, and K-band Satellite Communications.

Evaluation Boards are available upon request.

Lead-Free & RoHS compliant

*Note: Device is early in the characterization process prior to finalizing all electrical specifications. Specifications are subject to change without notice*

**TABLE I**  
**MAXIMUM RATINGS 1/**

| SYMBOL           | PARAMETER                         | VALUE         | NOTES        |
|------------------|-----------------------------------|---------------|--------------|
| V <sub>d</sub>   | Positive Supply Voltage           | 8 V           | <u>2/</u>    |
| V <sub>g</sub>   | Negative Supply Voltage Range     | -5 TO 0 V     |              |
| I <sub>d</sub>   | Positive Supply Current           | 1.75 A        | <u>2/</u>    |
| I <sub>g</sub>   | Negative Supply Current           | 35 mA         |              |
| P <sub>IN</sub>  | Input Continuous Wave Power       | 26 dBm        |              |
| P <sub>D</sub>   | Power Dissipation                 | 5.4 W         | <u>2/ 3/</u> |
| T <sub>CH</sub>  | Operating Channel Temperature     | 150 °C        | <u>3/ 4/</u> |
| T <sub>M</sub>   | Mounting Temperature (30 Seconds) | 260 °C        |              |
| T <sub>STG</sub> | Storage Temperature               | -65 to 150 °C |              |

- 1/ These ratings represent the maximum operable values for this device.
- 2/ Combinations of supply voltage, supply current, input power, and output power shall not exceed P<sub>D</sub>.
- 3/ When operated at this power dissipation with a base plate temperature of 70 °C, the median life time of 1.0E+6 hours.
- 4/ Junction operating temperature will directly affect the device median time to failure (MTTF). For maximum life, it is recommended that junction temperatures be maintained at the lowest possible levels.

**TABLE II**  
**THERMAL INFORMATION**

| PARAMETER                                                              | TEST CONDITIONS                                                                                                                                                 | T <sub>CH</sub><br>(°C) | θ <sub>JC</sub><br>(°C/W) | T <sub>M</sub><br>(HRS) |
|------------------------------------------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------|-------------------------|---------------------------|-------------------------|
| θ <sub>JC</sub> Thermal Resistance<br>(channel to backside of package) | V <sub>d</sub> = 6 V<br>I <sub>d</sub> = 825 mA<br>P <sub>diss</sub> = 4.95 W<br>Small Signal<br>T <sub>base</sub> = 70°C                                       | 143                     | 14.8                      | 1.8E+6                  |
| θ <sub>JC</sub> Thermal Resistance<br>(channel to backside of package) | V <sub>d</sub> = 6 V<br>I <sub>d</sub> = 970 mA @<br>P <sub>sat</sub><br>P <sub>diss</sub> = 4.4 W<br>P <sub>out</sub> = 1.4 W (RF)<br>T <sub>base</sub> = 70°C | 135                     | 14.8                      | 3.8E+6                  |

Note: Backside of package is the 70°C baseplate temperature. Thermal transfer is from the backside of the package through the board. The board must be designed to assure adequate thermal transfer from the package. Worst case condition is with no RF applied, 100% of DC power is dissipated.

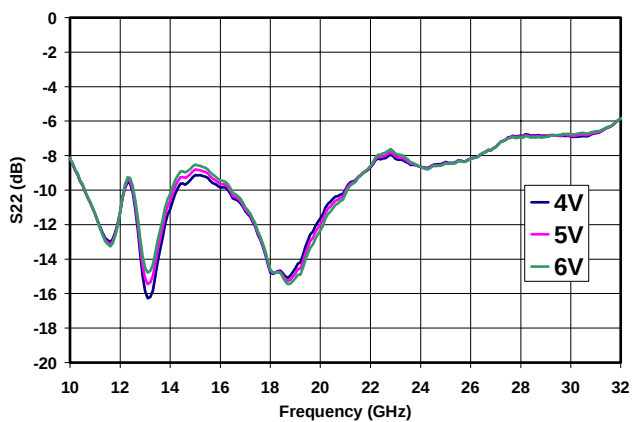
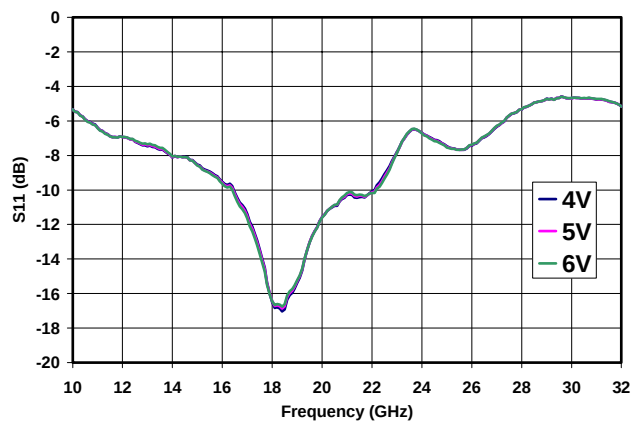
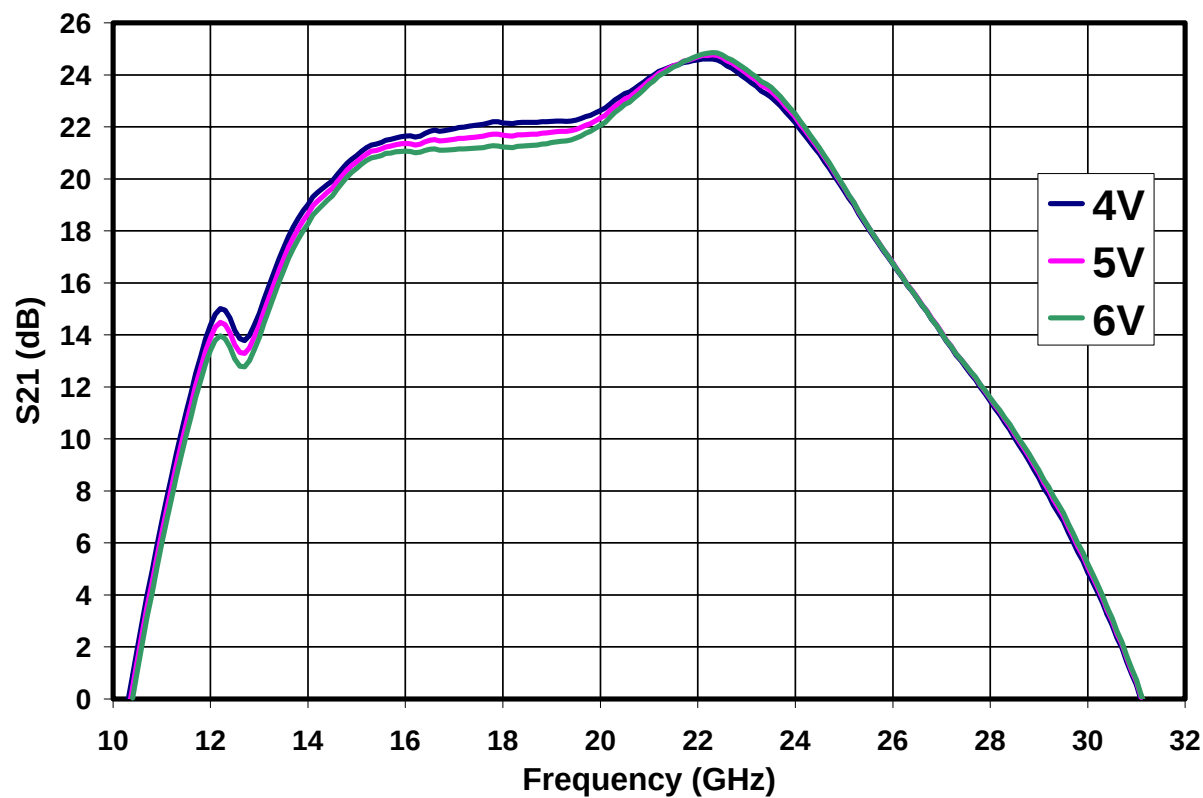
**TABLE III**  
**ELECTRICAL CHARACTERISTICS**  
(Ta = 25° C Nominal)

| PARAMETER                                 | TYPICAL | UNITS |
|-------------------------------------------|---------|-------|
| Frequency Range                           | 17 - 21 | GHz   |
| Drain Voltage, Vd                         | 6       | V     |
| Drain Current, Id                         | 825     | mA    |
| Gate Voltage Typical, Vg                  | -0.5    | V     |
| Small Signal Gain, S21                    | 21      | dB    |
| Input Return Loss, S11                    | 12      | dB    |
| Output Return Loss, S22                   | 12      | dB    |
| Reverse Isolation, S12                    | 55      | dB    |
| Saturated Output Power @ 16 dBm Pin, Psat | 31      | dBm   |
| Output Power @ 1dB Gain Compression, P1dB | 29      | dBm   |
| Output Third Order Intercepted Point      | 41      | dBm   |
| Small Signal Gain Temperature Coefficient | -0.03   | dB/°C |

## Measured Performance

$V_d = 4\text{--}6\text{V}$ ,  $I_{dq} = 825\text{mA}$

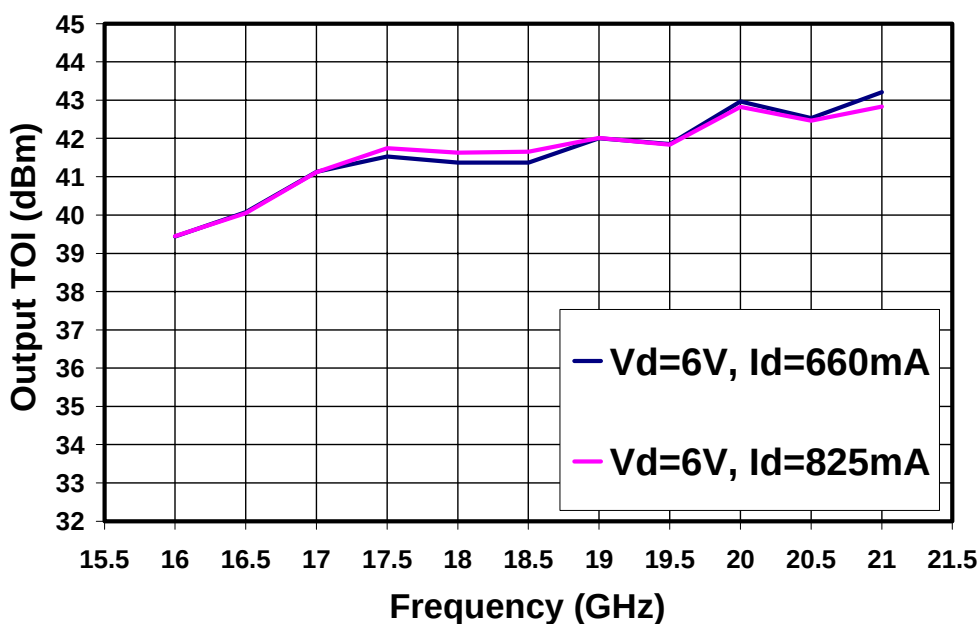
$V_g = -0.5\text{ V (typ.)}$



## Measured Performance

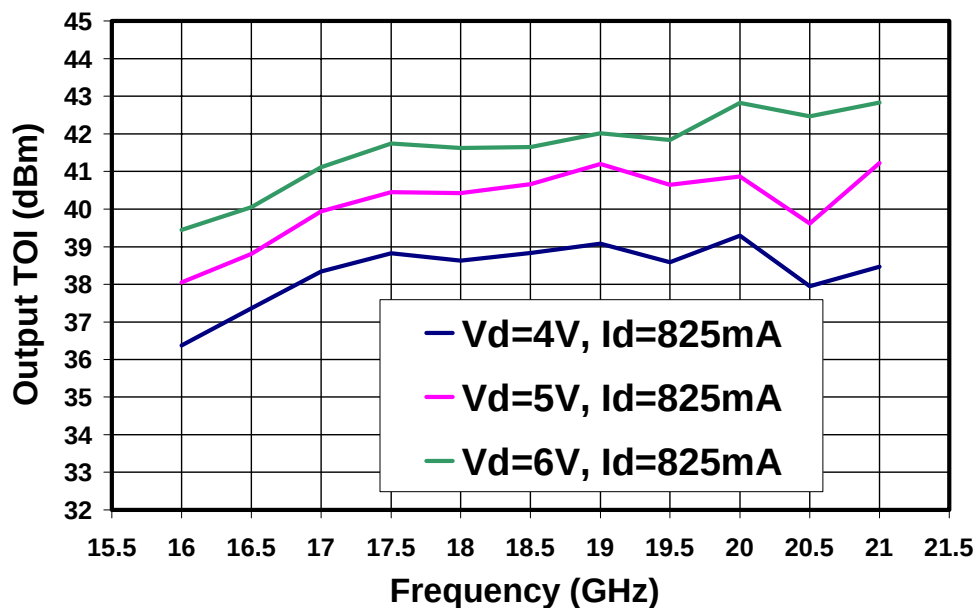
Vd = 6V, Id = 660, 825mA

Vg = -0.5 V (typ.)



Vd = 4-6V, Id = 825mA

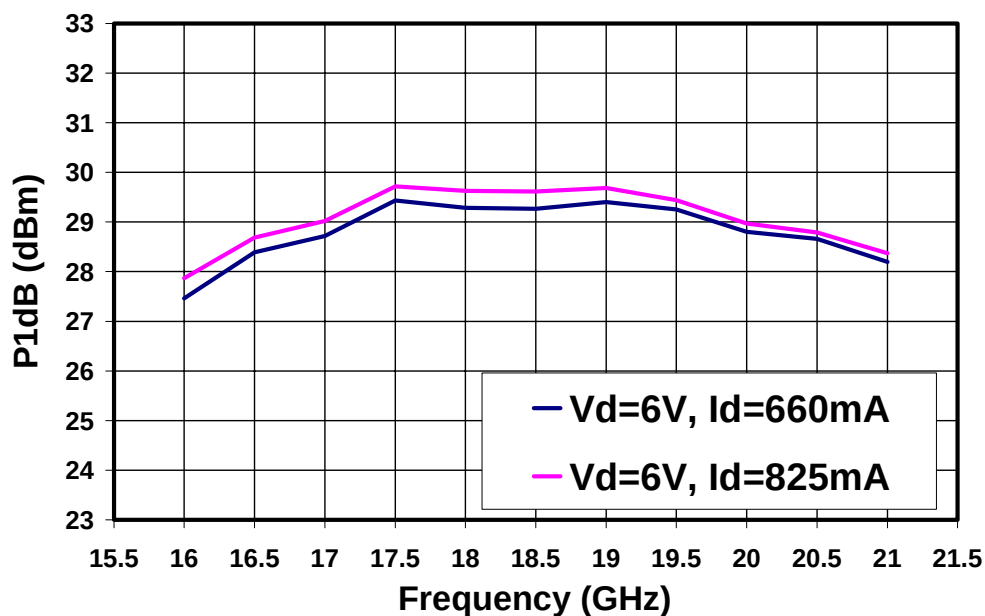
Vg = -0.5 V (typ.)



## Measured Performance

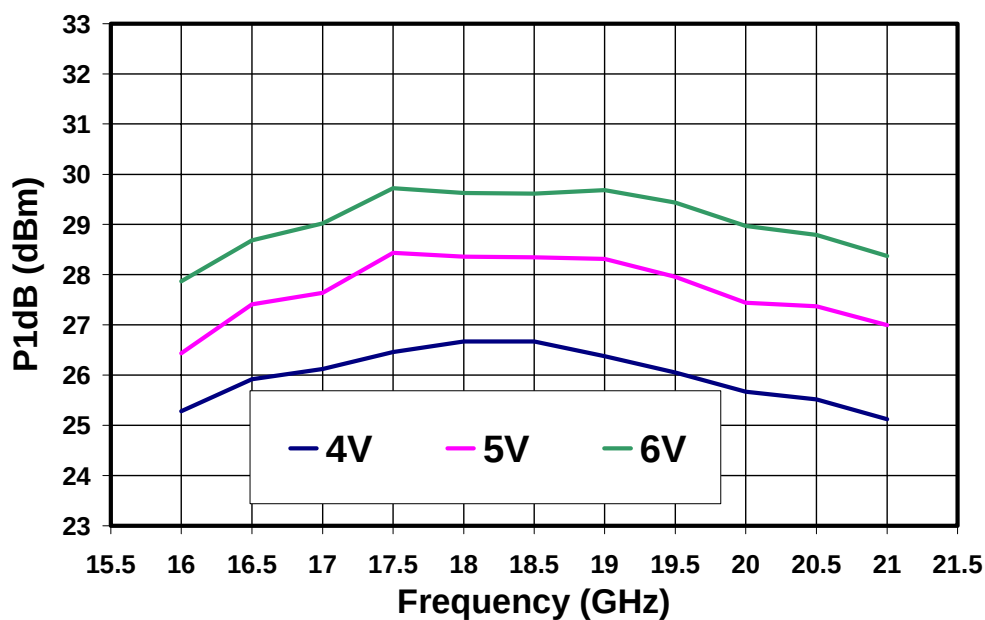
$V_d = 6V$ ,  $I_{dQ} = 660, 825mA$

$V_g = -0.5 V$  (typ.)



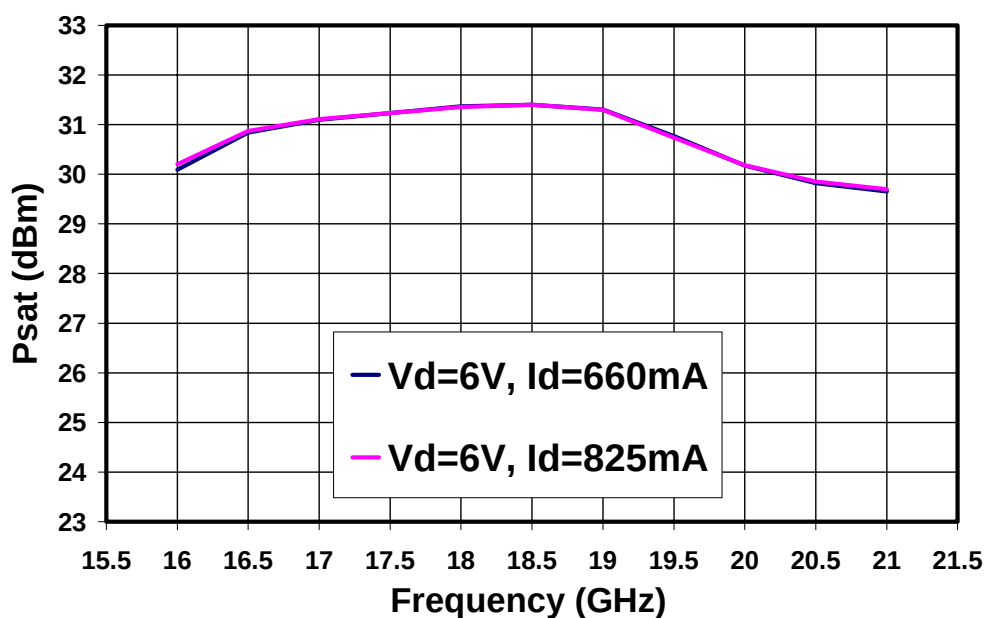
$V_d = 4-6V$ ,  $I_{dQ} = 825mA$

$V_g = -0.5 V$  (typ.)

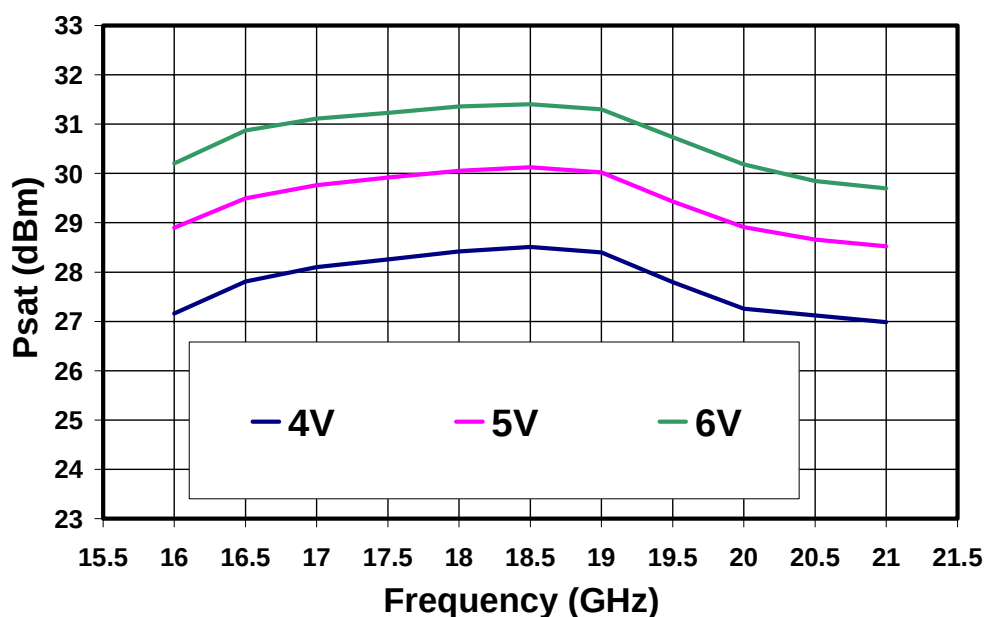


## Measured Performance

$V_d = 6V$ ,  $I_{dq} = 660, 825mA$   
 $V_g = -0.5 V$  (typ.)



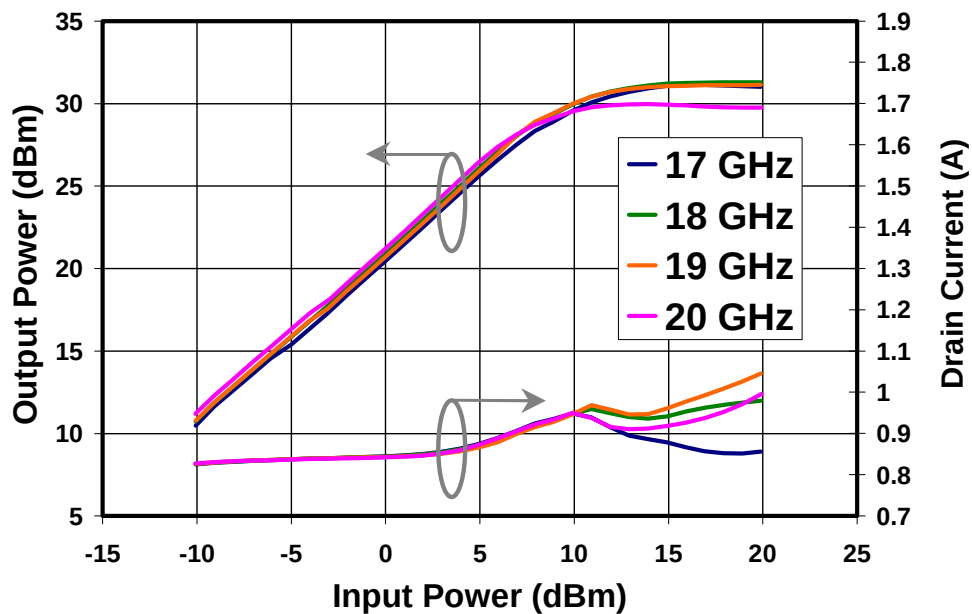
$V_d = 4-6V$ ,  $I_{dq} = 825mA$   
 $V_g = -0.5 V$  (typ.)



## Measured Performance

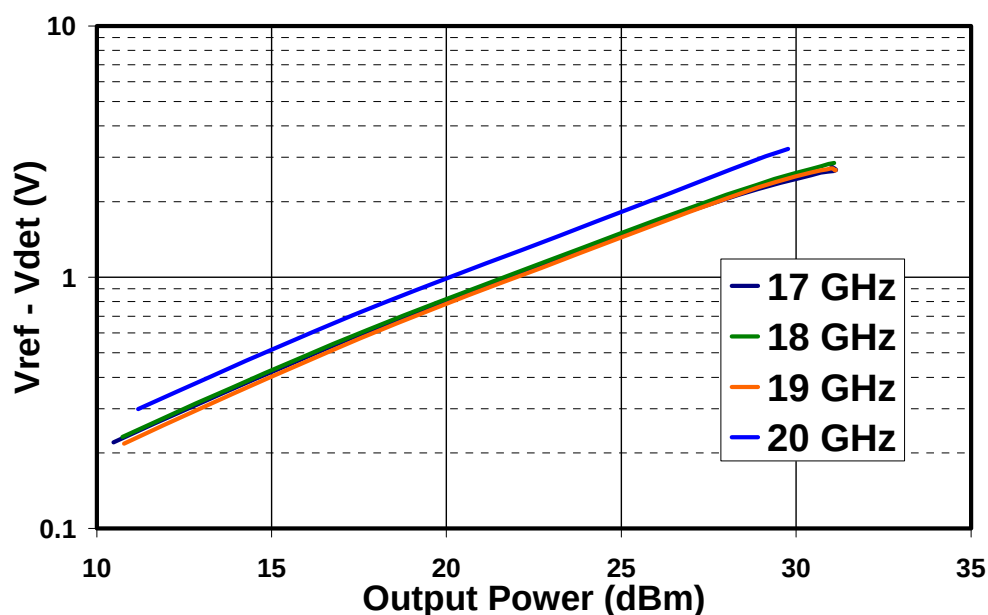
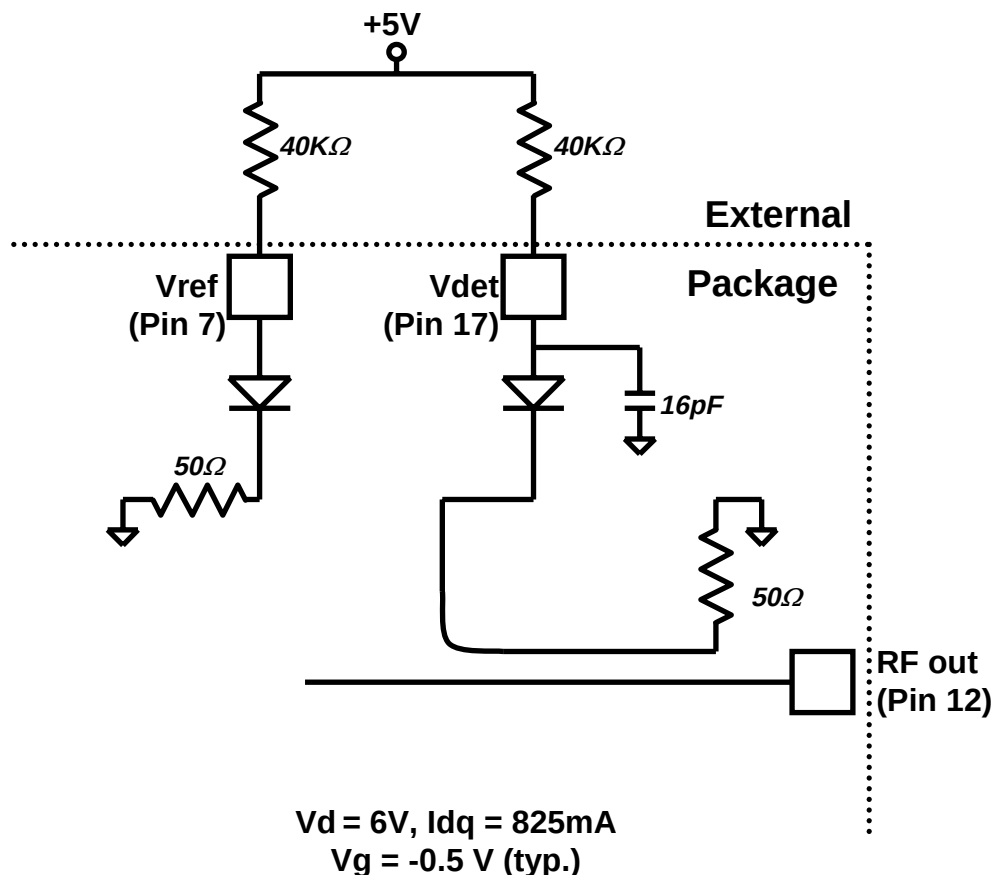
$V_d = 6V$ ,  $I_{dQ} = 825mA$

$V_g = -0.5V$  (typ.)

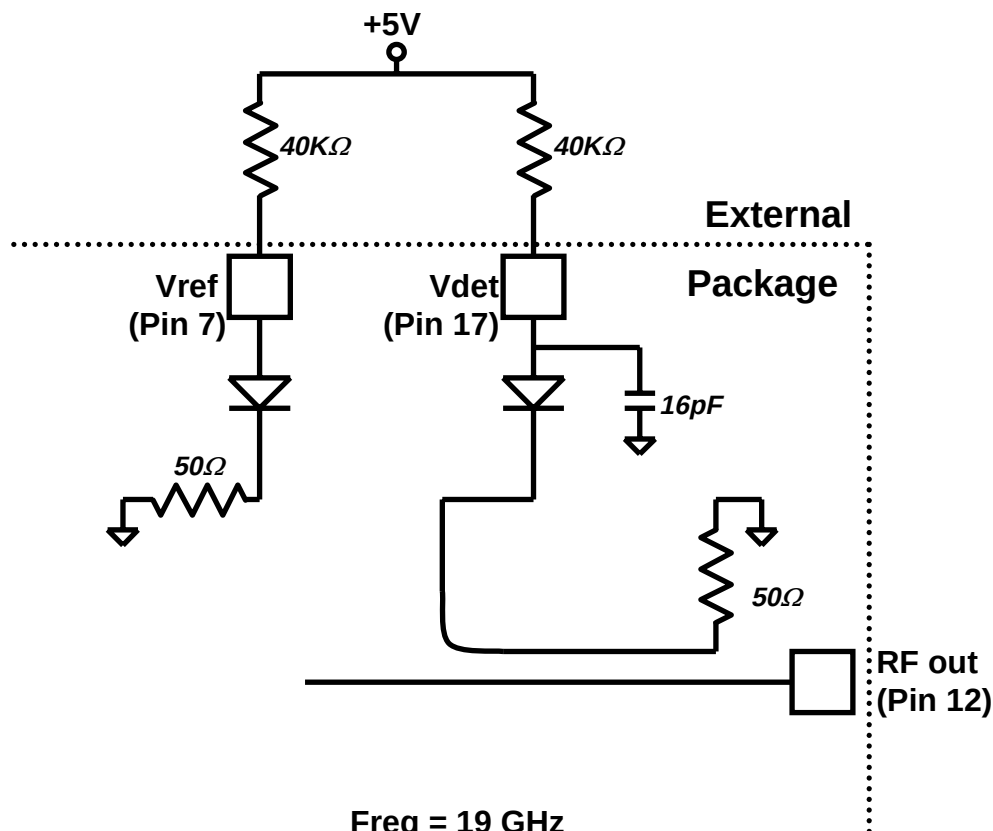




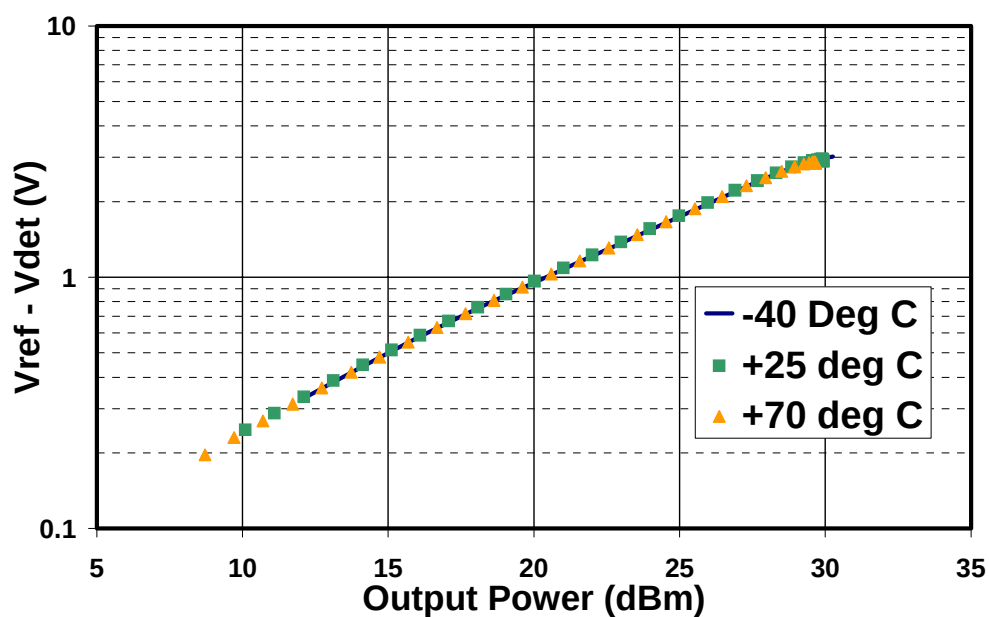
## Power Detector



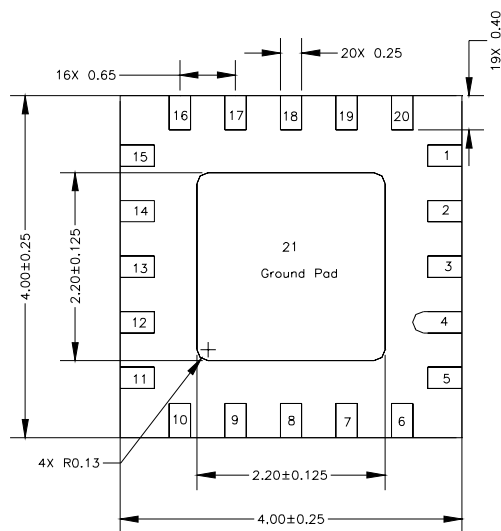
## Power Detector



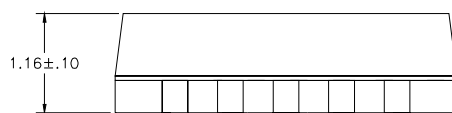
Freq = 19 GHz  
Vd = 6V, Idq = 825mA  
Vg = -0.5 V (typ.)



# Mechanical Drawing



BOTTOM VIEW



SIDE VIEW

Dimensions are in millimeters

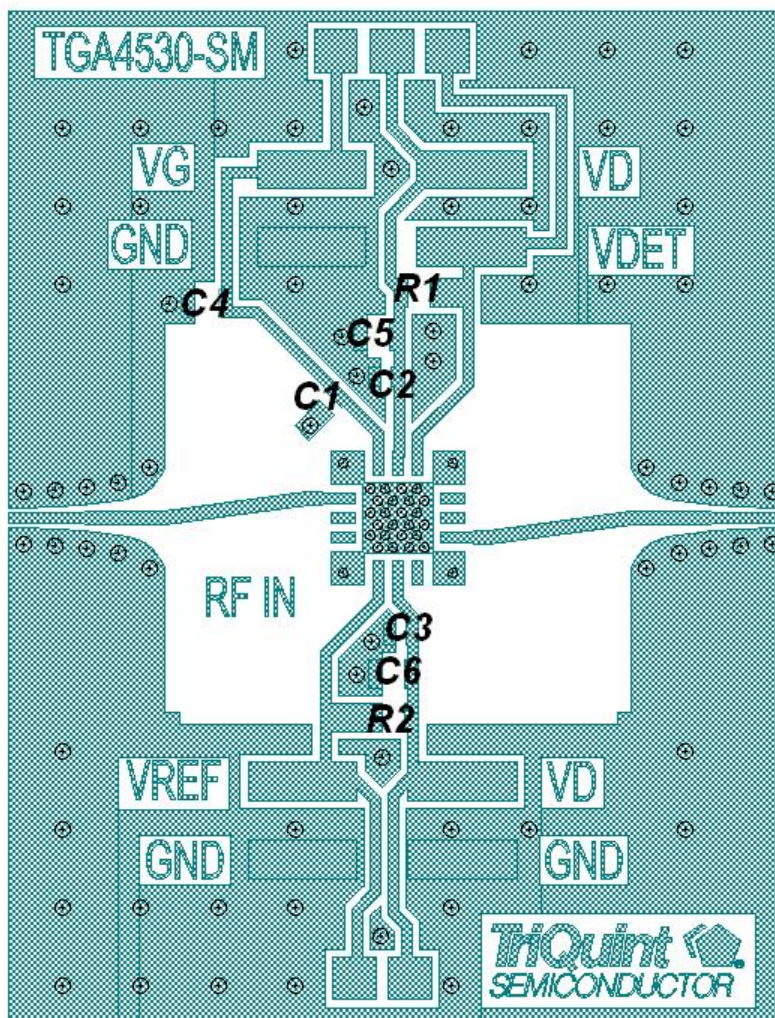
Dot on topside indicates Pin 1

Tolerances: ±0.076, unless otherwise noted

| Pin                             | Description |
|---------------------------------|-------------|
| 1, 5, 6, 10, 11, 15, 16, 20, 21 | GND         |
| 3, 4, 9, 13, 14                 | NC          |
| 2                               | RF Input    |
| 19                              | Vg          |
| 8 and 18                        | Vd          |
| 12                              | RF Output   |
| 17                              | Vdet        |
| 7                               | Vref        |

**GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.**

**Recommended Evaluation Board Layout Assembly \***



| Designator | Component         |
|------------|-------------------|
| C1,C2,C3   | 100pF Capacitor   |
| C4,C5,C6   | 1uF Capacitor     |
| R1,R2      | 40.2kOhm Resistor |

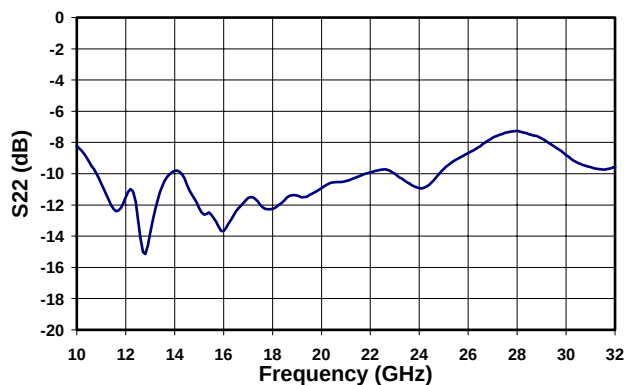
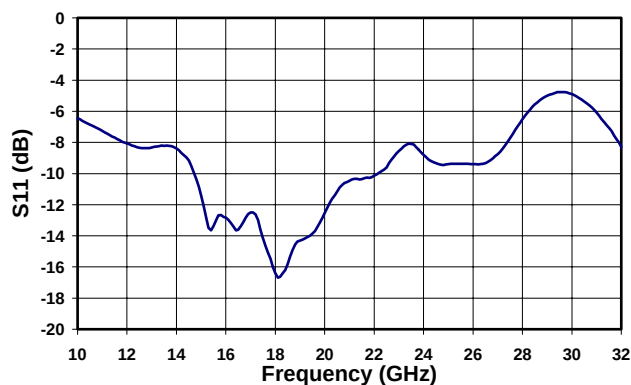
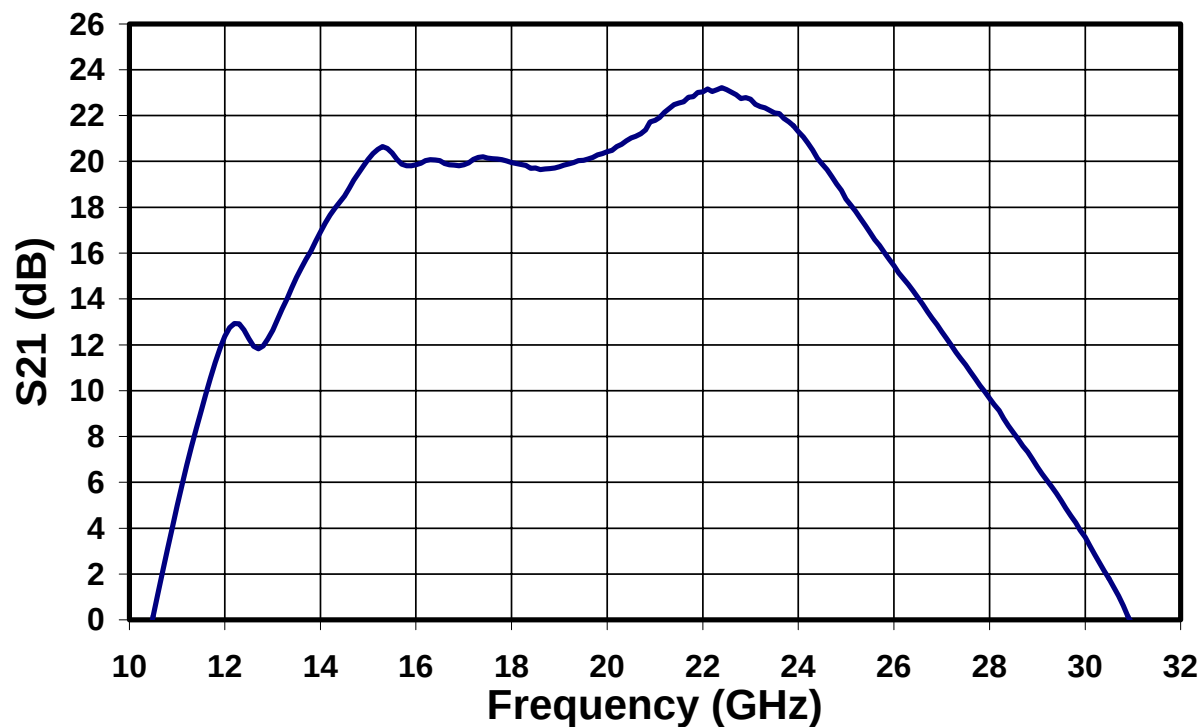
\* PCB is RO4003 8 mil thickness, 0.5 oz standard copper cladding, with Er = 3.38.

**GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.**

## Measured Performance - Evaluation Board

$V_d = 6V$ ,  $I_d = 825mA$

$V_g = -0.5V$  (typ.)

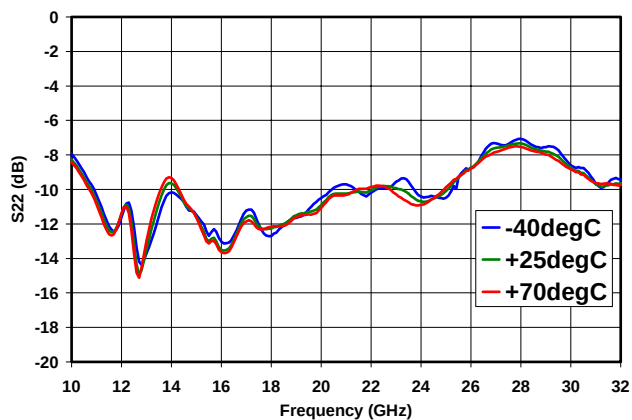
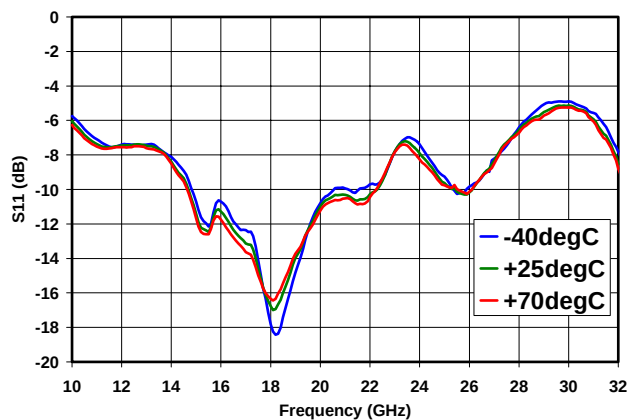
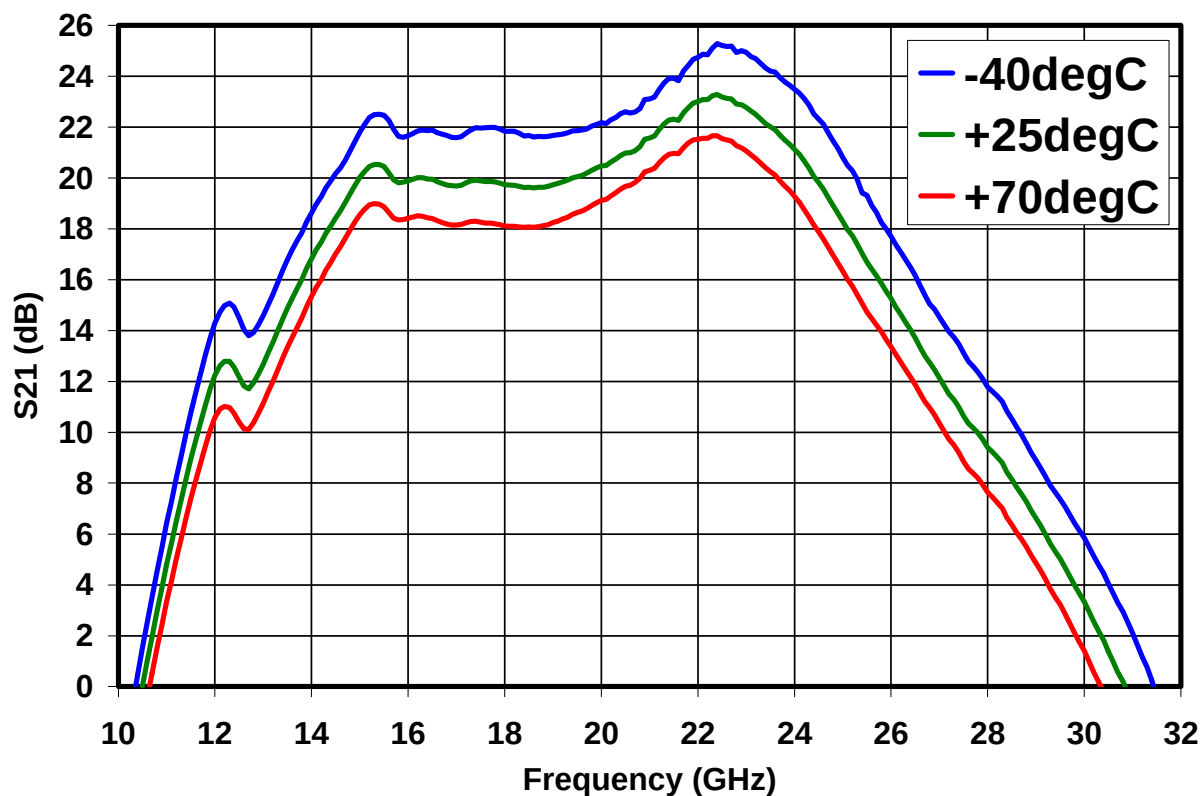


## Measured Performance - Evaluation Board

Data includes connector and board losses

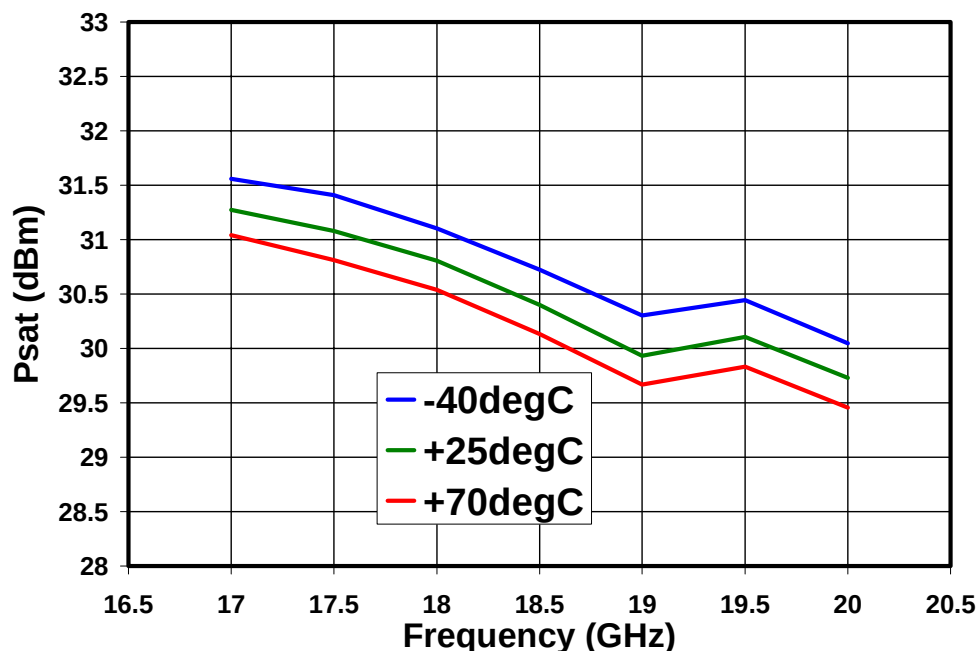
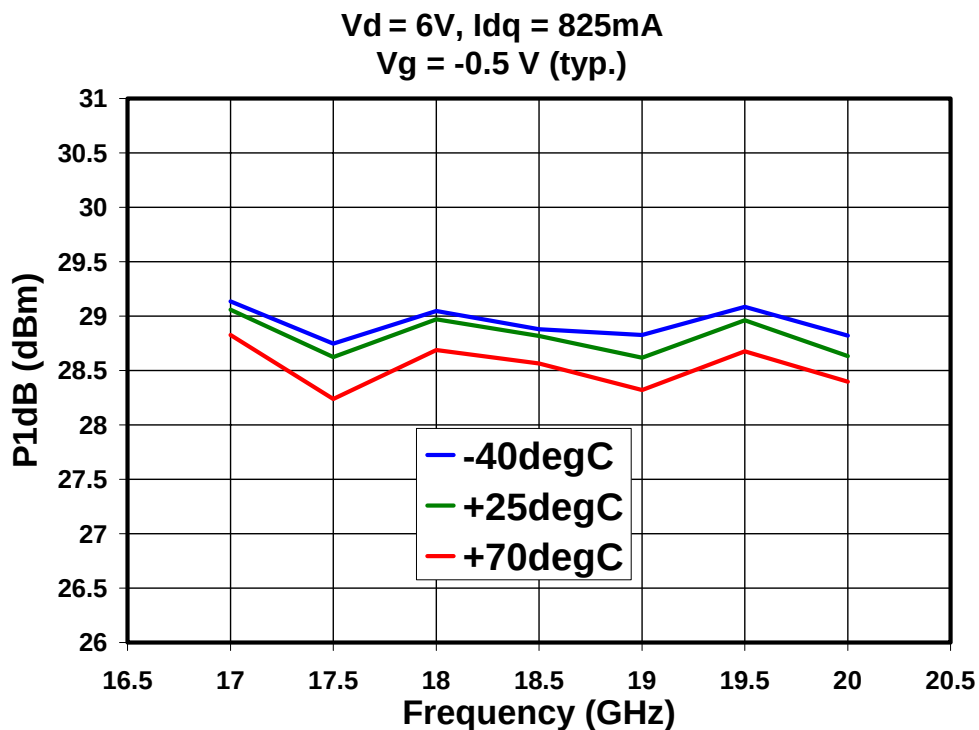
$V_d = 6V$ ,  $I_d = 825mA$

$V_g = -0.5V$  (typ.)



## Measured Performance - Evaluation Board

Data includes connector and board losses



## Recommended Surface Mount Package Assembly

Proper ESD precautions must be followed while handling packages.

Clean the board with acetone. Rinse with alcohol. Allow the circuit to fully dry.

TriQuint recommends using a conductive solder paste for attachment. Follow solder paste and reflow oven vendors' recommendations when developing a solder reflow profile. Typical solder reflow profiles are listed in the table below.

Hand soldering is not recommended. Solder paste can be applied using a stencil printer or dot placement. The volume of solder paste depends on PCB and component layout and should be well controlled to ensure consistent mechanical and electrical performance.

Clean the assembly with alcohol.

## Typical Solder Reflow Profiles

| Reflow Profile                       | SnPb                        | Pb Free                     |
|--------------------------------------|-----------------------------|-----------------------------|
| Ramp-up Rate                         | 3 °C/sec                    | 3 °C/sec                    |
| Activation Time and Temperature      | 60 – 120 sec @ 140 – 160 °C | 60 – 180 sec @ 150 – 200 °C |
| Time above Melting Point             | 60 – 150 sec                | 60 – 150 sec                |
| Max Peak Temperature                 | 240 °C                      | 260 °C                      |
| Time within 5 °C of Peak Temperature | 10 – 20 sec                 | 10 – 20 sec                 |
| Ramp-down Rate                       | 4 – 6 °C/sec                | 4 – 6 °C/sec                |

## Ordering Information

| Part       | Package Style         |
|------------|-----------------------|
| TGA4530-SM | QFN 4x4 Surface Mount |